



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	l _D max T _A = +25°C
30V	23mΩ @ V _{GS} = 10V	10A
30 V	33mΩ @ V _{GS} = 4.5V	8A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features and Benefits

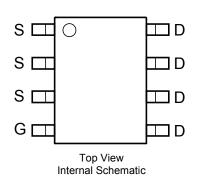
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Low Gate Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

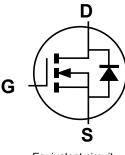
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.074 grams (approximate)



Top View





Equivalent circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG4466SSSL-13	SO-8	2500 / Tape & Reel

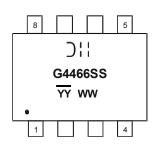
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

Notes:

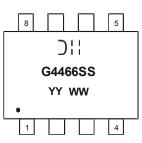
and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

) | | = Manufacturer's Marking G4466SS = Product Type Marking Code YYWW = Date Code Marking YY or \overline{YY} = Year (ex: 13 = 2013) WW = Week (01 - 53) YY = Date Code Marking for SAT (Shanghai Assembly/ Test site) YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +85°C	Ι _D	10 6	А
Pulsed Drain Current (Note 5)			I _{DM}	60	A
Avalanche Current (Notes 6)			I _{AR}	16	A
Repetitive Avalanche Energy (Notes 6) L = 0.1mH			E _{AR}	12.8	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.42	W
Thermal Resistance, Junction to Ambient @TA = 25°C (Note 5)	R _{0JA}	88.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_		V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	-	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	1.0	1.45	2.4	V	V_{DS} = V_{GS} , I_D = 250 μ A	
Static Drain-Source On-Resistance	р	_	15 25	23 33	mΩ	V _{GS} = 10V, I _D = 10A	
Static Drain-Source On-Resistance	R _{DS (ON)}					V _{GS} = 4.5V, I _D = 7.5A	
Forward Transfer Admittance	Y _{fs}	_	2.5	-	S	V _{DS} = 5V, I _D = 10A	
Diode Forward Voltage	V _{SD}	_	0.69	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	C _{iss}	_	478.9		pF		
Output Capacitance	C _{oss}		96.7		pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	61.4	_	pF		
Gate Resistance	Rg	0.4	1.1	1.6	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = 4.5V)	Qg		5.0	8	nC		
Total Gate Charge (V _{GS} = 10V)	Qg		10.5	17	nc		
Gate-Source Charge	Q _{gs}		1.8		nC V _{DS} = 15V, V _{GS} = 10V, I _D =		
Gate-Drain Charge	Q _{gd}	_	1.6		nC		
Turn-On Delay Time	t _{D(on)}	_	2.9		ns		
Turn-On Rise Time	tr	_	7.9		ns	V _{GS} = 10V, V _{DS} = 15V, R _G = 3Ω, R _L = 1.5Ω	
Turn-Off Delay Time	t _{D(off)}	_	14.6		ns		
Turn-Off Fall Time	t _f	_	3.1	_	ns	1	

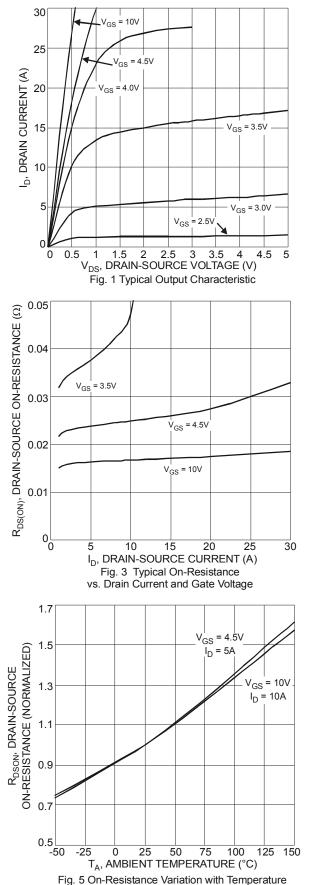
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

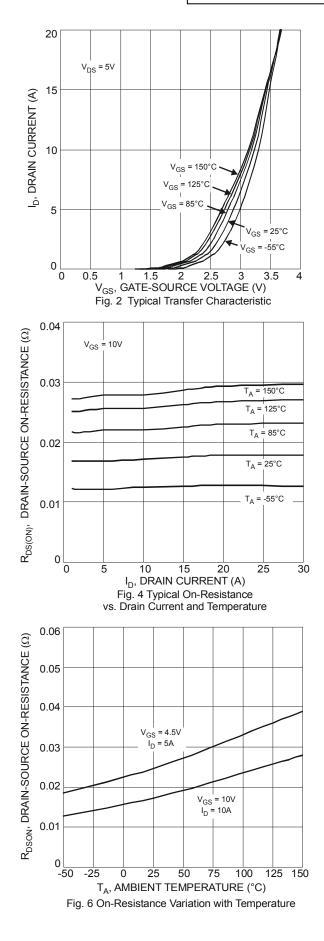
6. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = 25°C

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

DMG4466SSSL









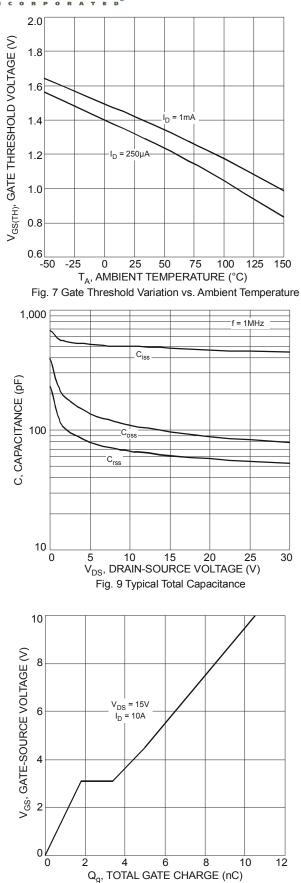
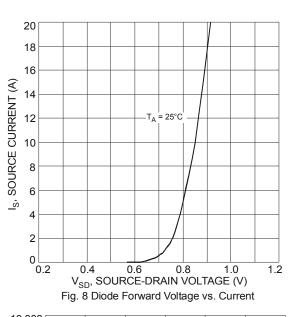
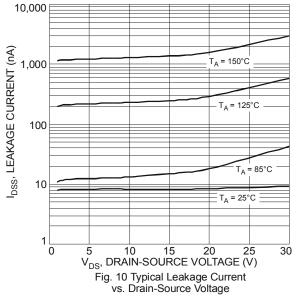


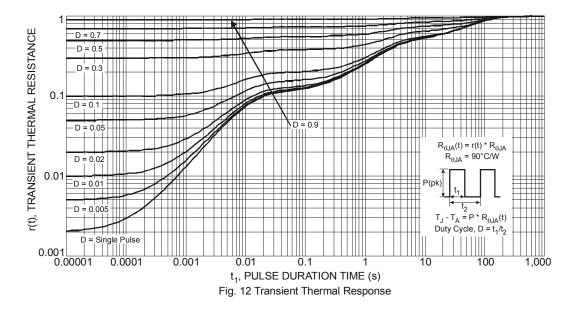
Fig. 11 Gate-Charge Characteristics





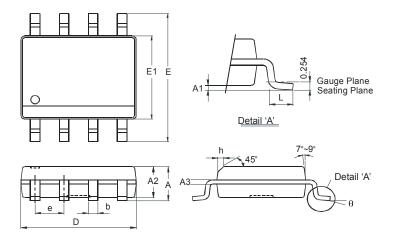






Package Outline Dimensions

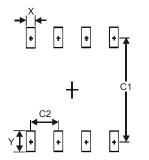
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)		
X	0.60		
Y	1.55		
C1	5.4		
C2	1.27		



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